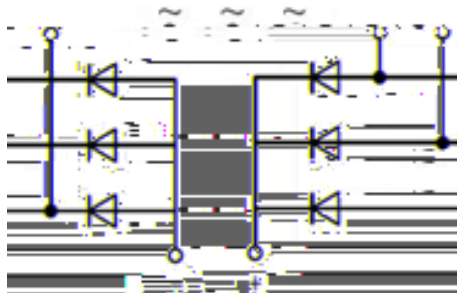




/R IRU DUG RODJHDGG@DNJHF UHQ
/R LGG F DQFH SDFNDJH
+WK V UHF UHQ FDSDELO

550		
, 7 °C		
) 60 3 PV		
) 0 D		

) HGV SSO IRU PRRU
/LH UHF ILHU/IRU UDQV/RUL HG PRRURQRU
1 RQRQRU@UHF ILHU/IRU FRQ HUH



7 QDW RKHU LVH VSHFILLHG

5HSHLLH SHDNUH HUH RODJH	7 M	550		
1RQUHSHLLH SHDNUH HUH RODJH	7 M	560		
HUJHIRU DUGF UHQ	7	,		
)RU DUGV UHF UHQ	F F@ 6LQ D H + 7 M	,)60		
, DOHIRUI VQJ		,		V
506 LVRO IRQ RODJH	+ V P LQ	,62		
- QF IRQ HP SHUD UH UDQJH		7 M		
6 RUDJH HP SHUD UH UDQJH		7VJ		



7

QDW RKHU LH VS FILLG

FIG.1: Forward characteristics(per diode)

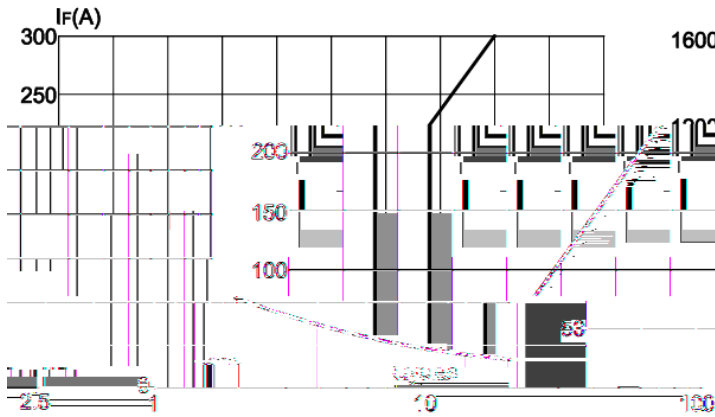


FIG.2: Peak on-state surge current

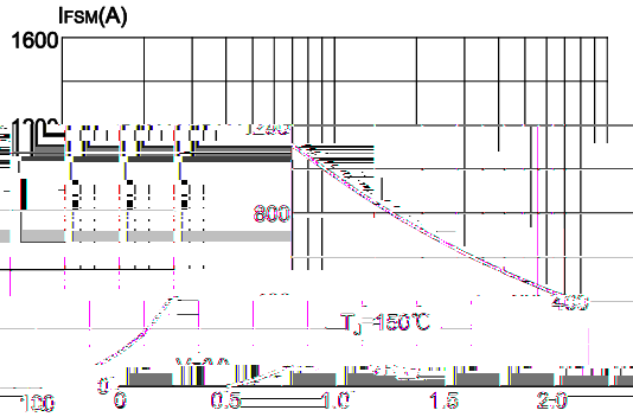


FIG.4: Maximum transient thermal impedance

$R_{th(j-c)}$ (°C/W) Junction-to-case(per diode)

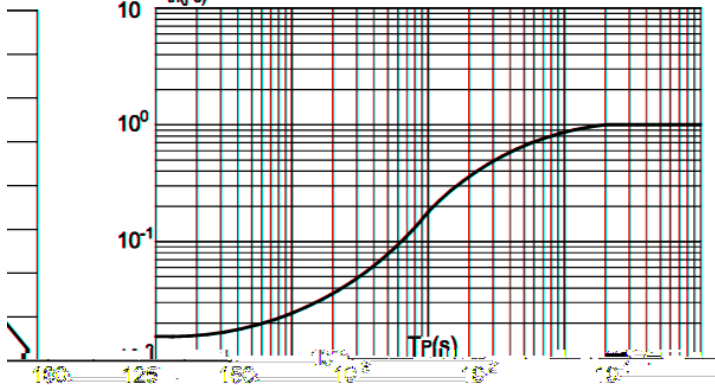
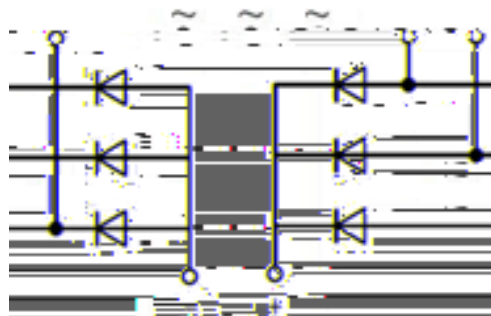
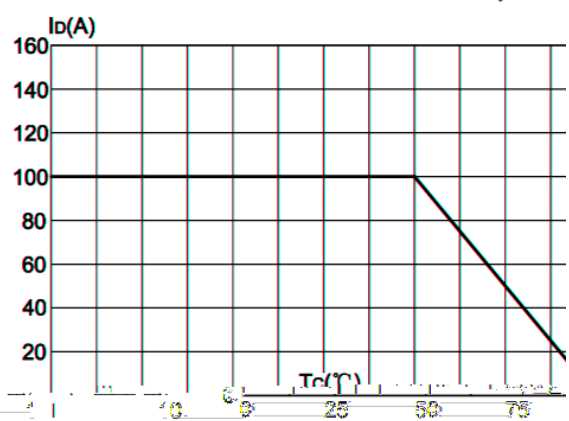
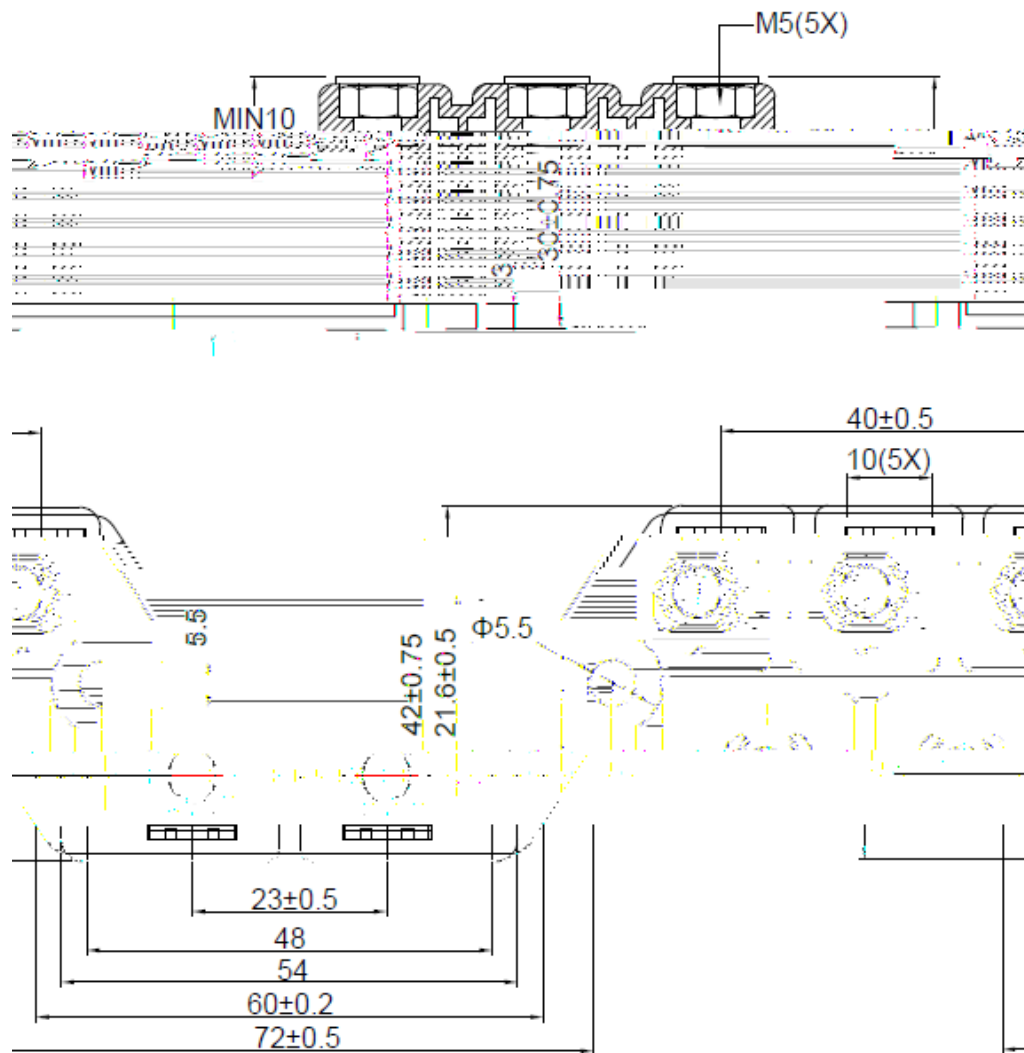


FIG.3: Forward current vs. case temperature





8QL R PHDV UPHQ PP



,QRUPDIRQI UQVKG IQ KIV GRF PHQ IV EHOI HG R EH DFF UDH DQG UHODEI +R H HU
-IDQIV -IH-IH6HP IERQG FRU R / GDW PHVQR UHVSQMEIQ IRUKHFRQMT HQFHVR VH
LKR FROMGHU DIRQIRUV FK LQRUP DIRQQRU VEH RQGL 7KIV LQRUP DIRQIQ KIV GRF PHQ
LVV EWF RFKQIH LKR SURUQR IEH 1R LKVDQGLQ KIV -IDQIV -IH-IH 10 0 FRP SO
LK KH HUP VR QHG IQ D VJQHGDJUHHP HQ 3URG FV DQG LQRUP DIRQ SUR IGHG IQ KIV
GRF PHQ KD H QR IQUQHHP HQ RI SDHQV -IDQIV -IH-IH DW PHVQR UHVSQMEIQ IRUDQ
IQUQHHP HQ RI RKHUUKVRI KLGSDUHV KIEKPD UHV OIURP KH VRI V FK SURG FVDQG
LQRUP DIRQ 7KIV GRF PHQ IV KH IQIDOUHODVH QHG - O 7KIV GRF PHQ
V SHUHGHVDQGUHSDUHV DQ LQRUP DIRQSUH IR VO V SSQH

 LV UHUVHUG UDHPDUNRI -IDQIV -IH-IH6HP IERQG FRU R / -IDQIV -IH-IH
6HP IERQG FRU R / G QUKVUHUHG